

MBR2030CTLG

Switch-mode Dual Schottky Power Rectifier

Features and Benefits

- Highly Stable Oxide Passivated Junction
- Very Low Forward Voltage Drop (0.4 Max @ 10 A, $T_C = 150^\circ\text{C}$)
- High Junction Temperature
- High dv/dt Capability
- Excellent Ability to Withstand Reverse Avalanche Energy Transients
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 20 A Total (10 A Per Diode Leg)
- This Device is Pb-Free and is RoHS Compliant*

Applications

- Power Supply – Output Rectification
- Power Management – ORING
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Sec
- ESD Rating: Human Body Model 3B
Machine Model C



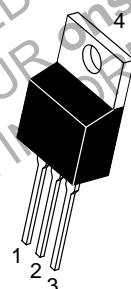
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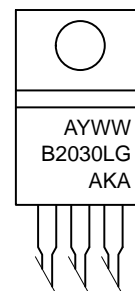
SCHOTTKY BARRIER RECTIFIER 20 AMPERES, 30 VOLTS



MARKING DIAGRAM



TO-220
CASE 221A
STYLE 6



A = Assembly Location
Y = Year
WW = Work Week
B2030L = Device Code
G = Pb-Free Package
AKA = Diode Polarity

ORDERING INFORMATION

| Device | Package | Shipping |
|-------------|---------------------|---------------|
| MBR2030CTLG | TO-220 (Pb-Free) | 50 Units/Rail |

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR2030CTLG

MAXIMUM RATINGS (Per Leg)

| Rating | Symbol | Value | Unit |
|---|---------------------------------|--------------|------------------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V_{RRM} V_{RWM} V_R | 30 | V |
| Average Rectified Forward Current ($T_C = 167^\circ\text{C}$) Per Diode Per Device | $I_{F(AV)}$ | 10 20 | A |
| Non-repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | I_{FSM} | 150 | A |
| Peak Repetitive Forward Current (Square Wave, 20 kHz, $T_C = 166^\circ\text{C}$) | I_{FRM} | 10 | A |
| Peak Repetitive Reverse Surge Current (2.0 μs , 1.0 kHz) | I_{RRM} | 1.0 | A |
| Operating Junction Temperature (Note 1) | T_J | - 65 to +175 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | - 65 to +175 | $^\circ\text{C}$ |
| Voltage Rate of Change (Rated V_R) | dv/dt | 1000 | V/ μs |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS (Per Leg)

| Characteristic | Symbol | Value | Unit |
|--|-----------------|-------|--------------------|
| Maximum Thermal Resistance, Junction-to-Case (Min. Pad) | $R_{\theta JC}$ | 2.0 | $^\circ\text{C/W}$ |
| Maximum Thermal Resistance, Junction-to-Ambient (Min. Pad) | $R_{\theta JA}$ | 60 | $^\circ\text{C/W}$ |

ELECTRICAL CHARACTERISTICS (Per Leg)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|--|--------|------------------|------------------------------|------------------------------|------|
| Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 10$ Amps, $T_J = 25^\circ\text{C}$) ($I_F = 10$ Amps, $T_J = 150^\circ\text{C}$) ($I_F = 20$ Amps, $T_J = 25^\circ\text{C}$) ($I_F = 20$ Amps, $T_J = 150^\circ\text{C}$) | V_F | - - - - | 0.45 0.32 0.51 0.41 | 0.52 0.40 0.58 0.48 | V |
| Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 100^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$) | I_R | - - - | 0.11 10 - | 5.0 40 75 | mA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle $\leq 10\%$.

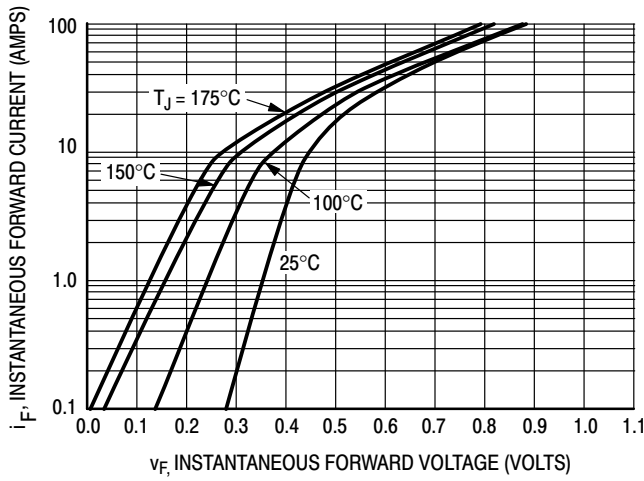


Figure 1. Typical Forward Voltage

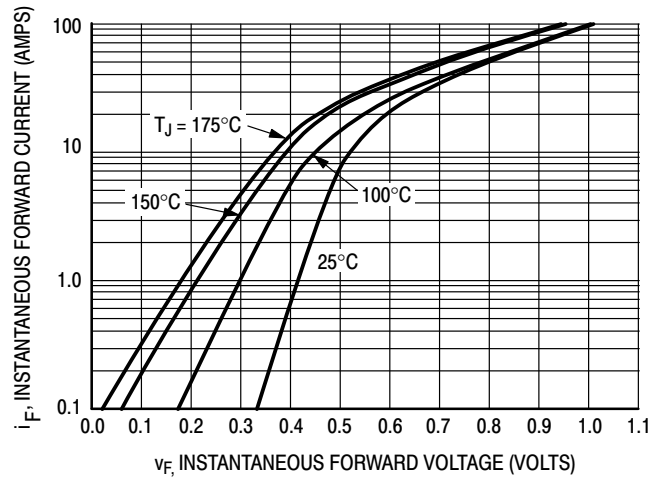


Figure 2. Maximum Forward Voltage

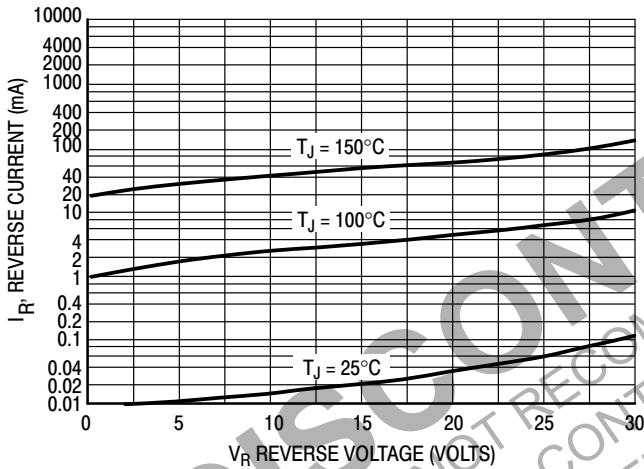


Figure 3. Typical Reverse Current

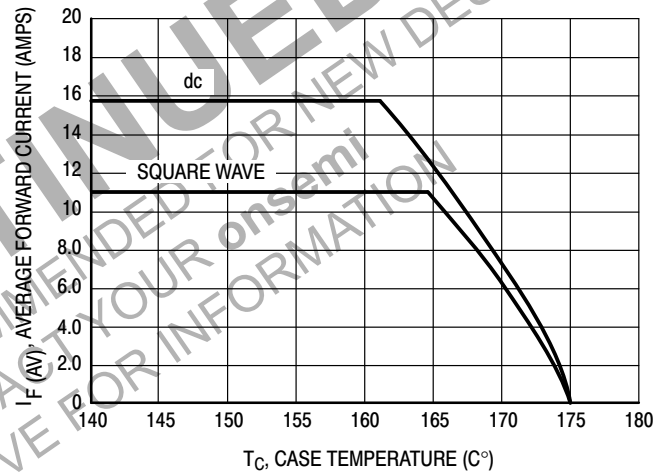


Figure 4. Current Derating, Case Per Leg

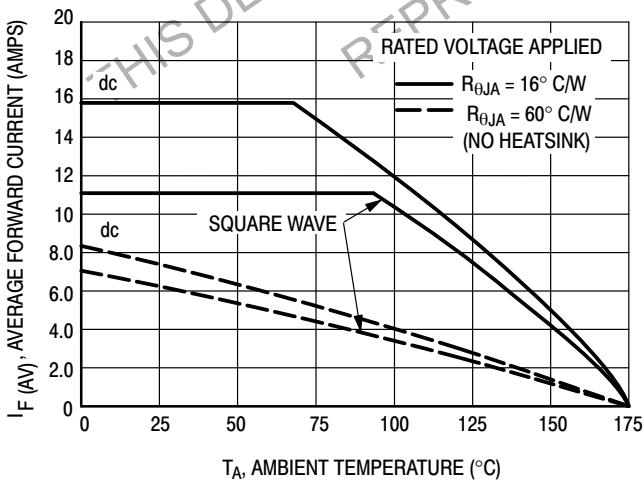


Figure 5. Current Derating, Ambient Per Leg

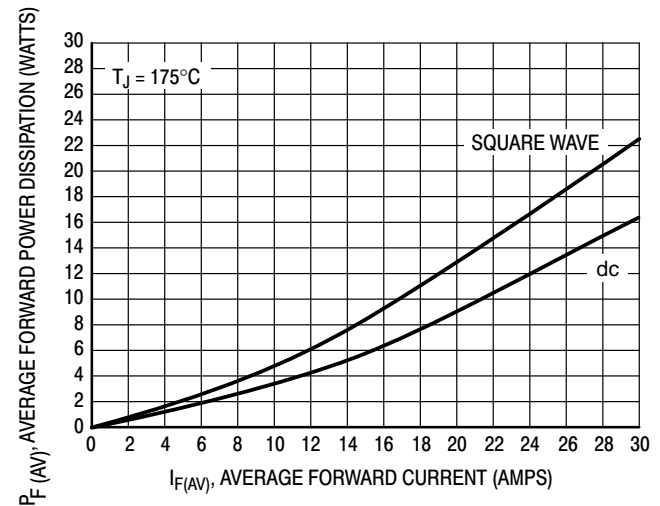


Figure 6. Forward Power Dissipation

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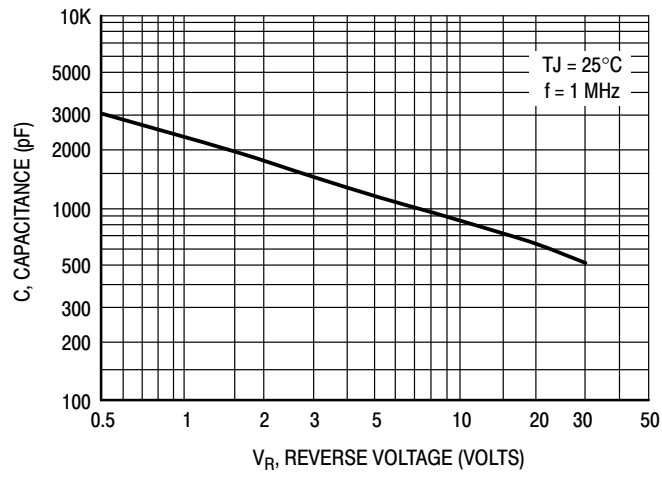
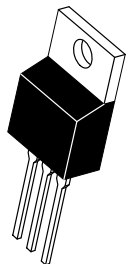
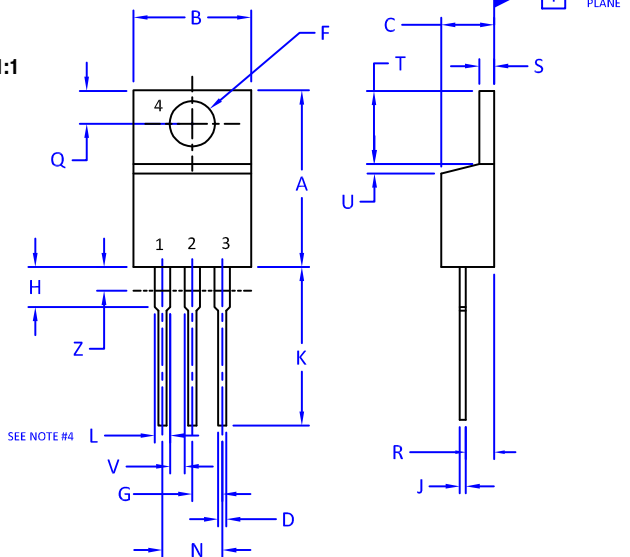


Figure 7. Typical Capacitance

DISCONTINUED
THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN
PLEASE CONTACT YOUR onsemi
REPRESENTATIVE FOR INFORMATION



SCALE 1:1



TO-220
CASE 221A
ISSUE AK

DATE 13 JAN 2022

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.415 | 9.66 | 10.53 |
| C | 0.160 | 0.190 | 4.07 | 4.83 |
| D | 0.025 | 0.038 | 0.64 | 0.96 |
| F | 0.142 | 0.161 | 3.60 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.161 | 2.80 | 4.10 |
| J | 0.014 | 0.024 | 0.36 | 0.61 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.41 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | ---- | 1.15 | --- |
| Z | ---- | 0.080 | --- | 2.04 |

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

| | | |
|------------------|-------------|---|
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